

Indian Institute of Technology, Delhi
Laser systems and applications (PHL 752)
Major

Duration : 2Hrs
Marks : 40

1. Explain the concept of frequency conversion using pulsed laser (as a tunable and/or white light laser) (5 marks) ✓
2. Draw schematic diagram of typical heterojunction (multilayer) laser diode device along with possible energy band diagram explaining the electron/hole transport mechanism. 4 marks ✓
3. Draw the construction of DFB and DBR lasers. ✓ 4 marks ✓
4. GaAs material (of length 350 μm) at 300K is injected with excess carriers of concentration $1.75 \times 10^{18} \text{cm}^{-3}$. When GaAs transparency limit of carrier concentration is $1.25 \times 10^{18} \text{cm}^{-3}$ and absorption coefficient is 600cm^{-1} , approximate the peak gain. 3 marks
5. One word/sentence answers:
 6. (a) Which laser frequency creates (theoretically) less heat affected zone when machining Vanadium ? ✓
 - (b) What material removal mechanism happens in lasik surgery?
 - (c) What is hybrid machining? ✓
 - d) Name the process in which cells be deposited without being punctured using lasers 4 marks
7. Explain the pulsed (nano and femtosecond) laser and material interaction at different time scales. Also explain various applications arise at different time scales of such interaction. 5+5 marks
8. What is the role of laser and optical filters in Raman spectroscopy ? 4 marks
9. (a) Draw a schematic diagram explaining the working of a free electron laser towards generation of THz pulses. (b) Explain the role of the semiconductor substrate in the detection of THz radiation and draw a schematic for gated THz detection. 3+3 marks